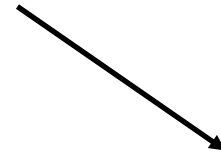


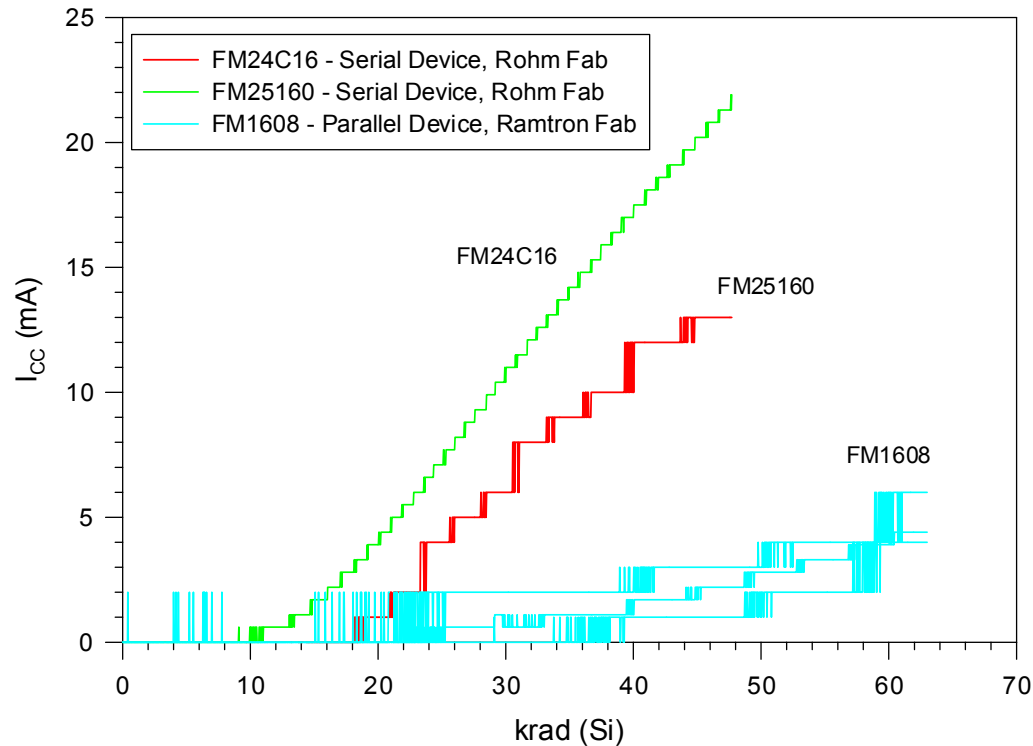
Miscellaneous

LVDO Regulator Failure

$V_{\text{OUT}} 3.3\text{V} \rightarrow 4.4\text{V}$
Destructive



FRAM Memory Functionality Loss During Total Dose Test



In situ static current measurements of two serial and one parallel FRAM device types. This initial study showed that Rohm (serial) and Ramtron research fab (parallel) devices could withstand moderate doses without significant leakage currents. Post irradiation testing of the FM1608 showed that all devices catastrophically failed. Annealing did not help. In situ functional tests or a step irradiation method are needed for determination of the functional limit. The base CMOS process is not the limiting factor for the FM1608.